

C 15644

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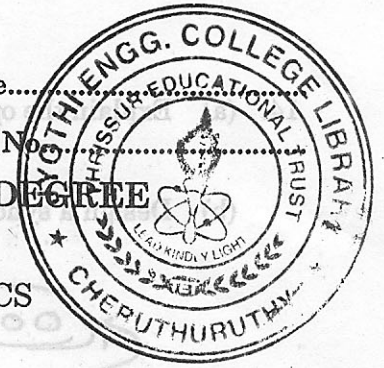
Name.....

Reg. No.....

**FOURTH SEMESTER B.TECH. (ENGINEERING) DEGREE  
EXAMINATION, JUNE 2011**

EE 09 405/PTEE 09 404—DIGITAL ELECTRONICS

(2009 Admissions)



Time : Three Hours

Maximum : 70 Marks

**Part A**

1. Define Propagation Delay.
2. Give the truth table of NAND and XNOR gate.
3. Differentiate between Combinational logic circuit and Sequential logic circuit.
4. How is JK FF converted to T FF ?
5. What is the function of program counter ?

(5 × 2 = 10 marks)

**Part B**

6. Compare CMOS and TTL technologies based on power dissipation voltage levels, noise immunity.
7. Perform the following operations in two's complement form :
  - (i)  $-36_H + 4 D_H$ .
  - (ii)  $-A F_H - 6C_H$ .
8. Draw the circuit of a full adder along with truth table.
9. Explain the 4-bit comparator circuit.
10. Draw and explain a static RAM cell and a dynamic RAM cell.
11. List the salient features of 8085 microprocessor.

(4 × 5 = 20 marks)

**Part C**

12. (a) Discuss the operation of CMOS inverter circuit with characteristics.

Or

- (b) Explain the schematic of 3 input TTL NAND gate.

13. (a) Construct a truth table for BCD to gray code converter and draw the simplified circuit schematic (Use Karnaugh map).

Or

- (b) (i) Differentiate between ROM, PLA and PAL.

(4 marks)

- (ii) Implement a  $4 \times 1$  multiplexer in the above 3 methods.

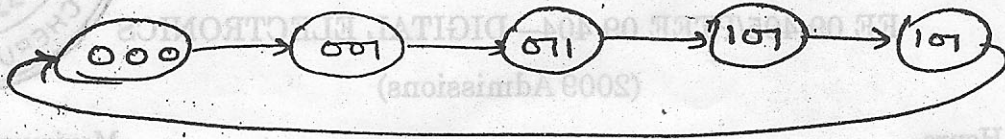
(6 marks)

Turn over

14. (a) Explain the operation of bidirectional shift register.

Or

(b) Design a synchronous counter for the state diagram given below :



Use D flip-flop.

15. (a) (i) Discuss the basic microcomputer operations.  
(ii) What are the various flags available and state their uses.

Or

(b) Write the VHDL code, using structural modelling for a full subtractor.

(4 × 10 = 40 marks)

(5 × 2 = 10 marks)

Part B

6. Compare CMOS and TTL technologies based on power dissipation voltage levels, noise immunity.

7. Perform the following operations in two's complement form :

- (i)  $-36_{10} + 41_{10}$
- (ii)  $-A_{16} - 6C_{16}$

8. Draw the circuit of a full adder along with truth table.

9. Explain the 4-bit comparator circuit.

10. Draw and explain a static RAM cell and a dynamic RAM cell.

11. List the salient features of 8085 microprocessor.

(4 × 5 = 20 marks)

Part C

12. (a) Discuss the operation of CMOS inverter circuit with characteristics.

Or

(b) Explain the schematic of 3 input TTL NAND gate.

18. (a) Construct a truth table for BCD to gray code converter and draw the simplified circuit schematic (Use Karnaugh map).

Or

(b) (i) Differentiate between ROM, PLA and PAL. (4 marks)

(ii) Implement a  $4 \times 1$  multiplexer in the above 3 methods. (6 marks)

Turn over